

# TO-220F Plastic-Encapsulate Transistors

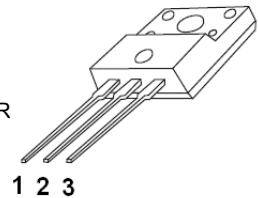
## KTD2061 TRANSISTOR (NPN)

### FEATURES

- High Breakdown Voltage
- High Transition Frequency
- High Current
- Complementary to KTB1369

### TO – 220F

1. BASE
2. COLLECTOR
3. EMITTER



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	180	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	2	A
P <sub>C</sub>	Collector Power Dissipation	2	W
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	62.5	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	200			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	180			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =200V, I <sub>E</sub> =0			1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =400mA	70		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =400mA		100		MHz

### CLASSIFICATION OF h<sub>FE</sub>

RANK	O	Y
RANGE	70-140	120-240